

Supplementary Materials: Photoluminescence of Layered Semiconductor Materials for Emission-Color Conversion of Blue Micro Light-Emitting Diode (μ LED)

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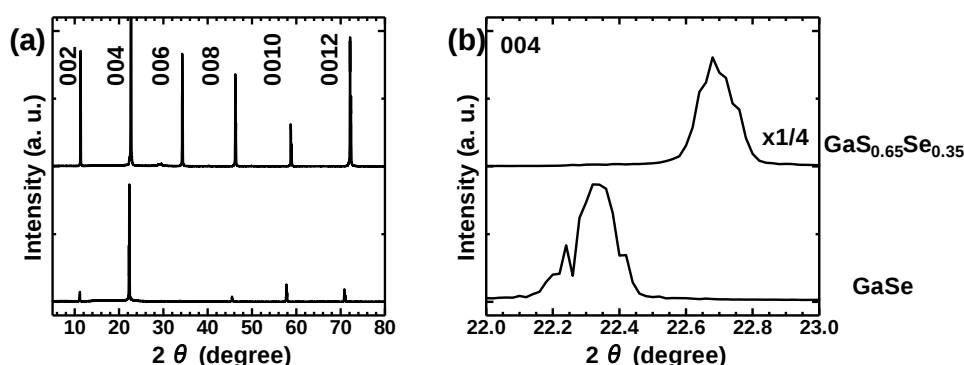


Figure S1. (a) Wide-range symmetrical 2θ XRD profiles for GaS_{0.65}Se_{0.35} and GaSe. (b) 004 peak region of 2θ XRD profiles. The lattice constant of GaS is $c = 15.492 \text{ \AA}$ (JCPDS Card No. 30-0576; P63/mmc). The lattice constant of GaSe is $c = 15.94 \text{ \AA}$ (JCPDS Card No. 03-065-3508; P63/mmc) [1].

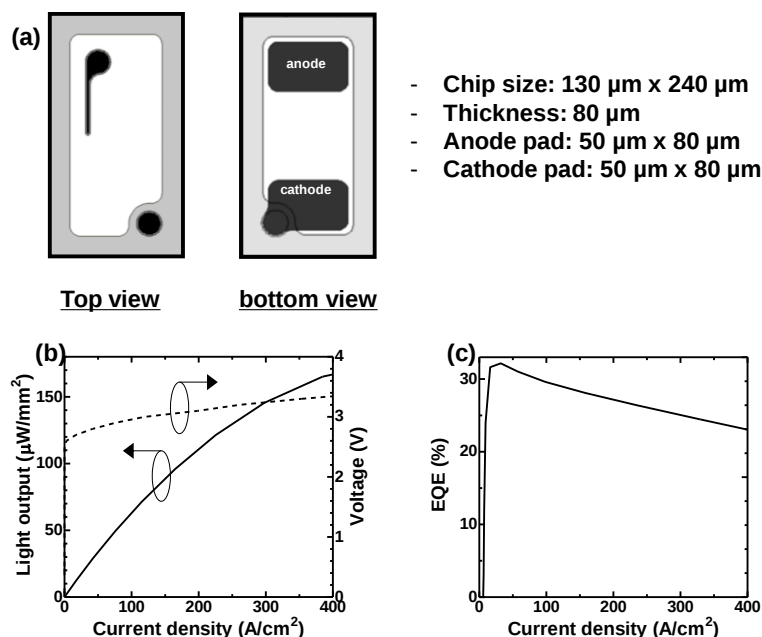


Figure S2. (a) Top view and bottom view of the device structures. Characteristics of used LED. (b) Current (I)-voltage (V)-Light output (L) characteristics of GaN-based μLED. (c) External quantum efficiency (EQE)-current (I) characteristic of GaN-based μLED.

References

1. Jung, C.S.; Park, K.; Shojaei, F.; Oh, J.Y.; Im, H.S.; Lee, J.A.; Jang, D.M.; Park, J.; Myoung, N.; Lee, C.-L.; et al. Photoluminescence and Photocurrents of $\text{GaS}_{1-x}\text{Se}_x$ Nanobelts. *Chem. Matter.* **2016**, *28*, 5811–5820, doi:10.1021/acs.chemmater.6b02101.



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